



# LC<sup>2</sup>MOS 16-Bit D/A Converter

ANALOG DEVICES INC

AD7846

## 1.1 Scope.

This specification covers the detail requirements for a monolithic CMOS 16-bit, voltage output, multiplying DAC, with a readback facility.

## 1.2 Part Number.

The complete part number is as follows:

Device	Part Number
-1	AD7846S(X)/883B

## 1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-M-1000; package outline:

(X)	Package	Description
D	D-28	28-Pin Side-Brazed Ceramic
E	E-28A	28-Terminal Leadless Ceramic Chip Carrier

## 1.3 Absolute Maximum Ratings. (T<sub>A</sub> = +25°C unless otherwise noted)

V <sub>DD</sub> to DGND	-0.3 V to +17 V
V <sub>CC</sub> to DGND	-0.3 V to +7 V
V <sub>SS</sub> to DGND	+3 V to -17 V
V <sub>REF+</sub> to DGND	±25 V
V <sub>REF-</sub> to DGND	±25 V
V <sub>OUT</sub> to DGND <sup>1</sup>	±25 V
R <sub>IN</sub> to DGND	±25 V
Digital Input Voltage to DGND	-0.3 V to V <sub>CC</sub> to +0.3 V
Digital Output Voltage to DGND	-0.3 V to V <sub>CC</sub> to +0.3 V
Power Dissipation (Any Package)	
to +75°C	1000 mW
Derates Above +75°C	10 mW/°C
Operating Temperature Range	-55°C to +125°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering 10 sec)	+300°C

### NOTE

<sup>1</sup>V<sub>OUT</sub> may be shorted to DGND, V<sub>DD</sub>, V<sub>SS</sub>, V<sub>CC</sub> provided that the power dissipation of the package is not exceeded.

## 1.5 Thermal Characteristics.

Thermal Resistance  $\theta_{JC} = 35^\circ\text{C}/\text{W}$  for D-28 and E-28A  
 $\theta_{JA} = 120^\circ\text{C}/\text{W}$  for D-28 and E-28A

Table 1.

Test	Symbol	Device	Design Limits $T_{min}-T_{max}$	Sub Group 1	Sub Group 2, 3	Sub Group 7, 8	Sub Group 9	Sub Group 10, 11	Sub Group 13, 14, 15	Test Condition <sup>1</sup>	Units
Relative Accuracy	$R_A$	1, 2	16	16	16					Unipolar Output <sup>2</sup>	$\pm$ LSB
Differential Nonlinearity <sup>3</sup>	DNL	1, 2	1	1	1						$\pm$ LSB
Gain Error <sup>4</sup>	$A_E$	1, 2	16	16	24						$\pm$ LSB
Offset Error	$O_E$	1, 2	16	16	24						$\pm$ LSB
Relative Accuracy	$R_A$	1, 2	8	8	8					Bipolar Output <sup>5</sup>	$\pm$ LSB
Differential Nonlinearity <sup>3</sup>	DNL	1, 2	1	1	1						$\pm$ LSB
Gain Error <sup>4</sup>	$A_E$	1, 2	8	16	16						$\pm$ LSB
Offset Error	$O_E$	1, 2	8	16	16						$\pm$ LSB
Bipolar Zero Error	$BIP_E$	1, 2	8	16	16						$\pm$ LSB
Reference Input Resistance	$V_{REFIN}$	1, 2	20/40	20/40	20/40					Resistance from $V_{REF-}$ to $V_{REF+}$	k $\Omega$ min/ max
$V_{REF+}$ Range	$V_{REF+}$	1, 2	6					6			$\pm$ V
$V_{REF-}$ Range	$V_{REF-}$	1, 2	6					6			$\pm$ V
Output Voltage Swing	$V_{SWING}$	1, 2	+4 -3					+4 -3	$V_{SS} + 4.0$ $V_{DD} - 3.0$		V
Input Voltage High Level	$V_{IH}$	1, 2	2.4	2.4	2.4						V
Input Voltage Low Level	$V_{IL}$	1, 2	0.8	0.8	0.8						V
Logical Input Current	$I_{IN}$	1, 2	10	10	10						$\pm$ $\mu$ A
Logical Input Capacitance	$C_{IN}$	1, 2	10					10			pF max
Output Voltage High Level	$V_{OH}$	1, 2	4.0	4.0	4.0					$I_{SOURCE} = 400 \mu A$	V min
Output Voltage Low Level	$V_{OL}$	1, 2	0.4	0.4	0.4					$I_{SINK} = 1.6 mA$	V max
Floating State Leakage Current		1, 2	10	10	10					DB0-DB15 = 0 to $V_{CC}$	$\pm$ $\mu$ A
Floating State Output Capacitance		1, 2	10					10			pF max
Positive Power Supply Current	$I_{DD}$	1, 2	5	5	5					$V_{OUT}$ Unloaded <sup>6</sup>	mA max
Negative Power Supply Current	$I_{SS}$	1, 2	5	5	5						mA max
Positive Logic Supply Current	$I_{CC}$	1, 2	1	1	1						mA max
Power Supply Sensitivity <sup>7</sup>	PSS	1, 2	2	2	2						LSB/V
Functional Test R/W to CS Setup Time	$t_1$	1, 2	50				40	50		See Figure 2 <sup>8</sup>	ns
CS Pulse Width (Write Cycle)	$t_2$	1, 2	140				150	190			ns
R/W to CS Hold Time	$t_3$	1, 2	50				40	50			ns
Data Setup Time	$t_4$	1, 2	120				110	120			ns
Data Hold Time	$t_5$	1, 2	0				0	0			ns
Data Access Time <sup>9</sup>	$t_6$	1, 2	320				230	320			ns
Bus Relinquish <sup>10</sup>	$t_7$	1, 2	90				80	90			ns
CLR Setup Time	$t_8$	1, 2	20				20	20		See Figure 2	ns
CLR Pulse Width	$t_9$	1, 2	150				150	150			ns
CLR Hold Time	$t_{10}$	1, 2	0				0	0			ns
LDAC Pulse Width	$t_{11}$	1, 2	100				80	100			ns
CS Pulse Width (Read Cycle)	$t_{12}$	1, 2	330				240	330			ns

NOTES

<sup>1</sup>Unless otherwise specified, 14.25 V dc  $\leq V_{DD} \leq 15.75$  V dc, -14.25 V dc  $\leq V_{SS} \leq -15.75$  V dc and 4.75 V dc  $\leq V_{CC} \leq 5.25$  V dc.  $V_{OUT}$  loaded with 3 k $\Omega$ , 1000 pF to 0 V.  $V_{REF+} = 5.0$  V dc.  $R_{IN}$  connected to 0 V. Parameters in subgroups 13, 14 15 are characterized at the initial design stage and after any subsequent redesigns.

<sup>2</sup> $V_{REF-} = 0$  V,  $V_{OUT} = 0$  V to 10 V, 1 LSB = 153  $\mu$ V.

<sup>3</sup>Monotonicity is guaranteed over full temperature range.

<sup>4</sup> $V_{OUT}$  load = 10 M $\Omega$ .

<sup>5</sup> $V_{REF-} = -5.0$  V,  $V_{OUT} = -10$  V to +10 V, 1 LSB = 305  $\mu$ V.

<sup>6</sup>The device is functional with a power supply of  $\pm 12$  V.

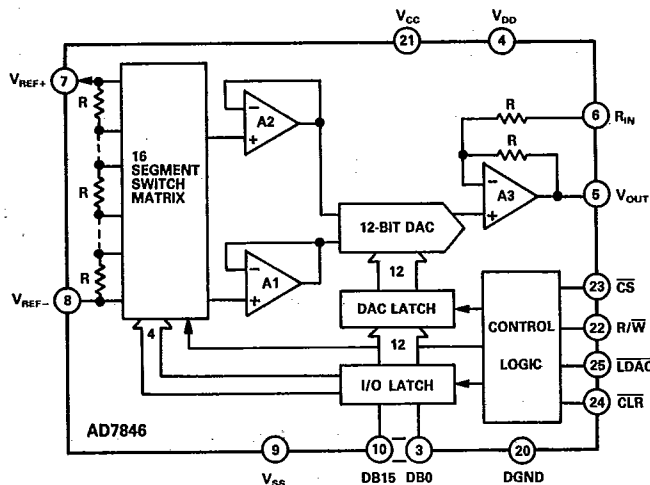
<sup>7</sup>Sensitivity of gain error, offset error and bipolar zero error to  $V_{DD}$ ,  $V_{SS}$  variations.

<sup>8</sup>All input control signals are specified with  $t_r = t_f = 5.0$  ns (10% to 90% of +5.0 V) and timed from a voltage level of 1.6 V.

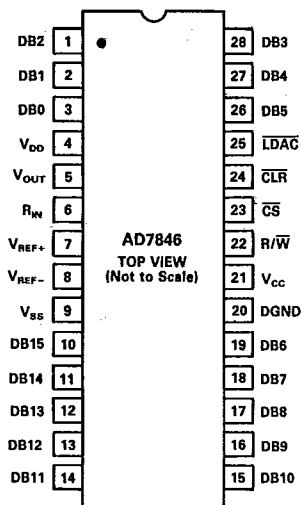
<sup>9</sup> $t_c$  is measured with the load circuits of Figure 1a and defined as the time required for an output to cross 0.8 V or 2.4 V.

<sup>10</sup> $t_r$  is defined as the time required for an output to change 0.5 V when loaded with the circuits of Figure 1b.

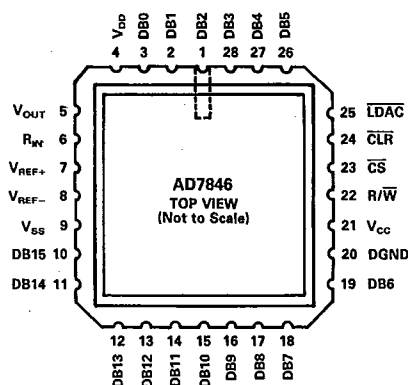
3.2.1 Functional Block Diagram and Terminal Assignments.



D Package (DIP)



E Package (LCC)



## Terminal Connections

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Device Type Case Outline Terminal Number	01 X Terminal Symbol	Device Type Case Outline Terminal Number	01 X Terminal Symbol
1	DB2	15	DB10
2	DB1	16	DB9
3	DB0	17	DB8
4	V <sub>DD</sub>	18	DB7
5	V <sub>OUT</sub>	19	DB6
6	R <sub>IN</sub>	20	DGND
7	V <sub>REF</sub> <sup>+</sup>	21	V <sub>CC</sub>
8	V <sub>REF</sub> <sup>-</sup>	22	R/ $\bar{W}$
9	V <sub>SS</sub>	23	$\bar{CS}$
10	DB15	24	$\bar{CLR}$
11	DB14	25	$\bar{LDAC}$
12	DB13	26	DB5
13	DB12	27	DB4
14	DB11	28	DB3

## Pin Descriptions

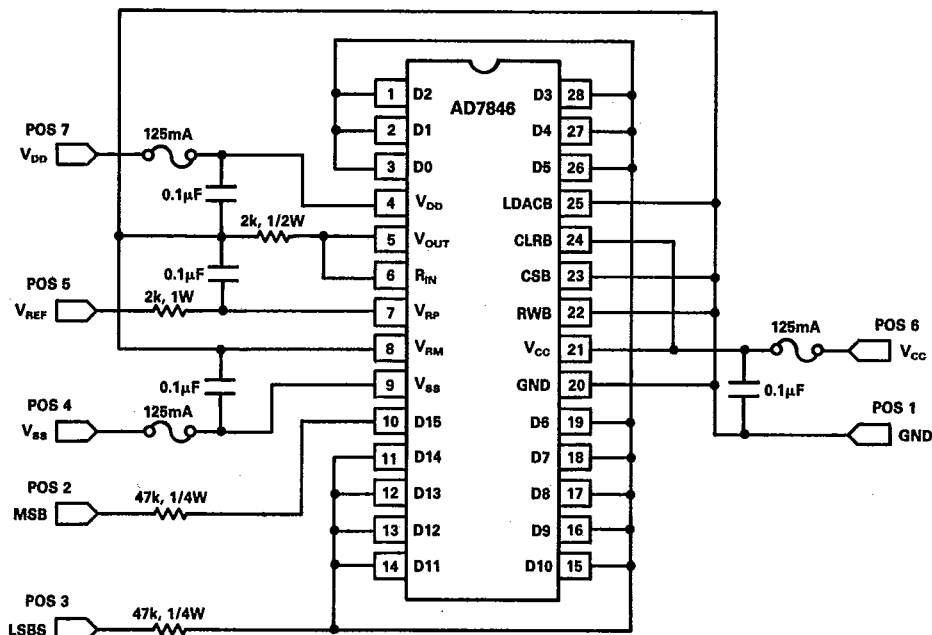
Pin	Description
DB2-DB0	Data I/O pins. DB0 is LSB.
V <sub>DD</sub>	Positive supply for analog circuitry. This is a +15 V nominal.
V <sub>OUT</sub>	DAC output voltage pin.
R <sub>IN</sub>	Input to summing resistor of DAC output amplifier. This is used to select output voltage ranges. See Tables 2 and 3.
V <sub>REF</sub> <sup>+</sup>	V <sub>REF</sub> <sup>+</sup> input. The DAC is specified for V <sub>REF</sub> <sup>+</sup> = 5.0 V.
V <sub>REF</sub> <sup>-</sup>	V <sub>REF</sub> <sup>-</sup> input. For unipolar operation connect it to -5.0 V. The device is specified for both conditions.
V <sub>SS</sub>	Negative supply for analog circuitry. This is -15 V nominal.
DB15-DB6	Data I/O pins. DB15 is MSB.
DGND	Ground pin for logic circuitry.
V <sub>CC</sub>	Positive supply for logic circuitry. This is +5.0 V nominal.
R/ $\bar{W}$	R/ $\bar{W}$ input. This can be used to load data to the DAC or read back the DAC latch contents.
$\bar{CS}$	Chip select input. This selects the device.
$\bar{CLR}$	Clear input. The DAC can be cleared to 000 . . . 000 or 100 . . . 000. See Tables 2 and 3.
$\bar{LDAC}$	Asynchronous load input to DAC.
DB5-DB3	Data I/O pins.

## 3.2.4 Microcircuit Technology Group.

This microcircuit is covered by technology group (80).

**4.2.1 Life Test/Burn-In Circuit.**

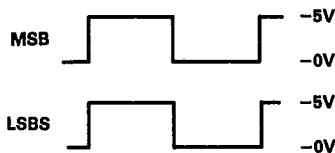
Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).



1. Each AD7846 socket has associated with it the four resistors shown, four 0.1 µF ceramic type capacitors and three 125 mA pico fuses.
2. Each burn-in board has the following seven external signals supplied:

Signal	Voltage
V <sub>DD</sub>	+15 V
V <sub>REF</sub>	+0 V
V <sub>CC</sub>	+5 V
GND	0 V
V <sub>SS</sub>	-15 V
MSB	See Below
LSBs	See Below

3. For static burn-in MSB and LSBs are both tied to +5 V.
4. For dynamic burn-in MSB and LSBs are driven with 20 kHz square waves as shown:



5. For static burn-in and power-up sequences is

1.  $V_{DD}$
2.  $V_{SS}$
3.  $V_{CC}$ , MSB, LSBs (together)
4.  $V_{REF}$

6. For dynamic burn-in the power sequence is

1.  $V_{DD}$
2.  $V_{SS}$
3.  $V_{CC}$
4. MSB, LSBs (together)
5.  $V_{REF}$

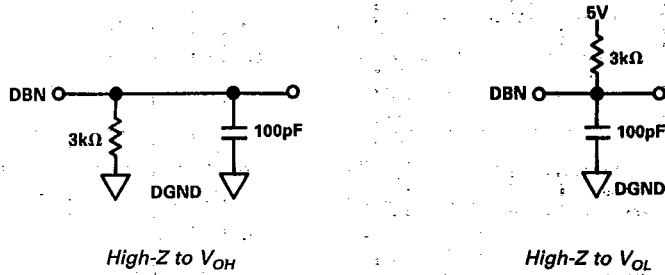


Figure 1a. Load Circuits for Access Time ( $t_a$ )

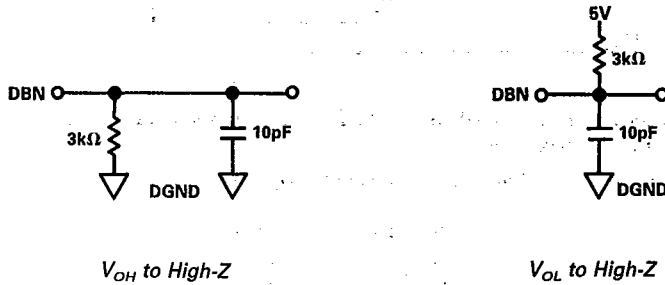


Figure 1b. Load Circuits for Bus Relinquish Time ( $t_r$ )

Figure 1. Load Circuits

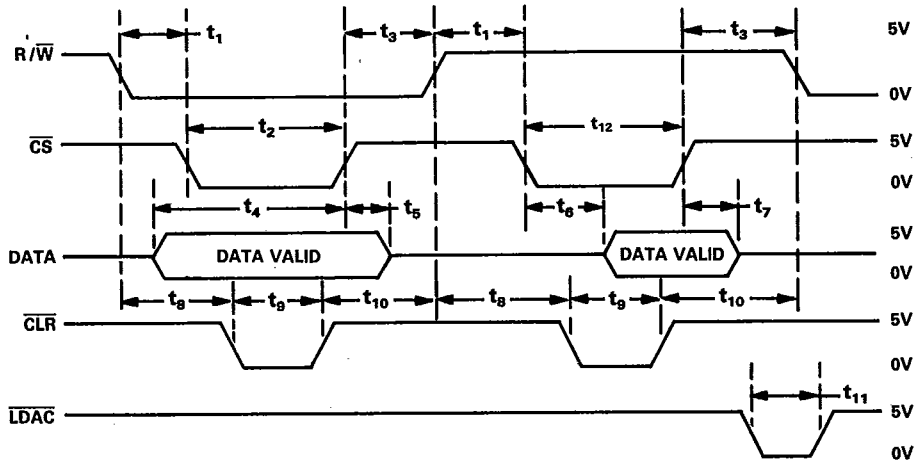


Figure 2. Switching Characteristics

Table 2. Truth Table

$\overline{CS}$	R/W	LDAC	$\overline{CLR}$	Function
1	X	X	X	3-State DAC I/O Latch in High Z-State
0	0	X	X	DAC I/O Latch Loaded with DB15-DB0
0	1	X	X	Contents of DAC I/O Latch Available on DB15-DB0
X	X	0	1	Contents of DAC I/O Latch Transferred to DAC Latch
X	0	X	0	DAC Latch Loaded with 000 . . . 000
X	1	X	0	DAC Latch Loaded with 100 . . . 000

0 = Low  
 1 = High  
 X = Don't Care

Table 3. Output Voltage Ranges

Output Range	$V_{REF+}$	$V_{REF-}$	$R_{IN}$
0 V to +5 V	+5 V	0 V	$V_{OUT}$
0 V to +10 V	+5 V	0 V	0 V
+5 V to -5 V	+5 V	-5 V	$V_{OUT}$
+5 V to -5 V	+5 V	0 V	+5 V
+10 V to -10 V	+5 V	-5 V	0 V

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